

BLF7G24L-160P; BLF7G24LS-160P

Power LDMOS transistor

Rev. 5 — 12 July 2013

Product data sheet

1. Product profile

1.1 General description

160 W LDMOS power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Test signal	f (MHz)	I_{DQ} (mA)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR _{885k} (dBc)
IS-95	2300 to 2400	1200	28	30	18.5	27.5	-45.5 ^[1]

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation (2300 MHz to 2400 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

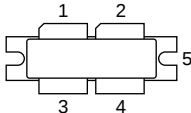
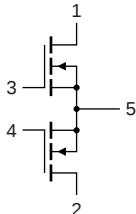
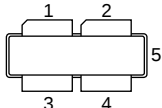
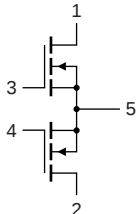
1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF7G24L-160P (SOT539A)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source		
[1]			
BLF7G24LS-160P (SOT539B)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source		
[1]			

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF7G24L-160P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A
BLF7G24LS-160P	-	earless flanged balanced ceramic package; 4 leads	SOT539B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ }^{\circ}\text{C}$; $P_L = 30\text{ W}$; $V_{DS} = 28\text{ V}$; $I_{Dq} = 1200\text{ mA}$	0.2	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$ per section, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 1\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 102\text{ mA}$	1.5	1.9	2.3	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	2.8	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	-	19	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	280	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 3.57\text{ A}$	-	6.9	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 3.57\text{ A}$	-	0.15	0.23	Ω

7. Test information

Remark: All testing performed in a class-AB production test circuit.

Table 7. Functional test information

Test signal: single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13).
PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz; $f_1 = 2300\text{ MHz}$;
 $f_2 = 2400\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 1200\text{ mA}$; $T_{case} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 30\text{ W}$	17.8	18.5	-	dB
RL_{in}	input return loss	$P_{L(AV)} = 30\text{ W}$	-	-13.5	-9	dB
η_D	drain efficiency	$P_{L(AV)} = 30\text{ W}$	25	27.5	-	%
$ACPR_{885k}$	adjacent channel power ratio (885 kHz)	$P_{L(AV)} = 30\text{ W}$	-	-45.5	-41.5	dBc

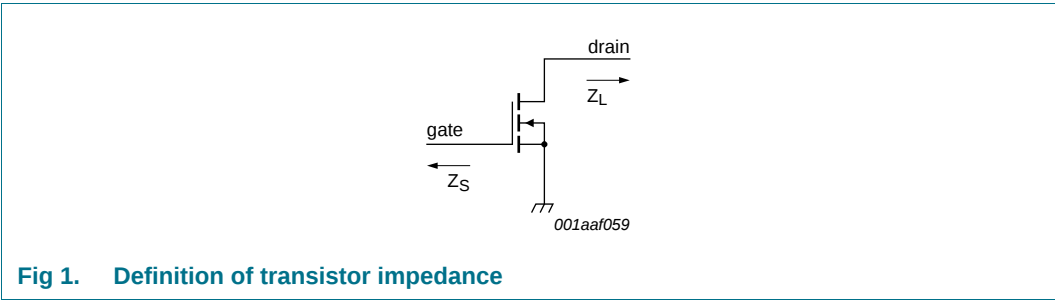
7.1 Ruggedness in class-AB operation

The BLF7G24L-160P and BLF7G24LS-160P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28\text{ V}$; $I_{Dq} = 1200\text{ mA}$; $P_L = 160\text{ W}$; $f = 2300\text{ MHz}$.

7.2 Impedance information

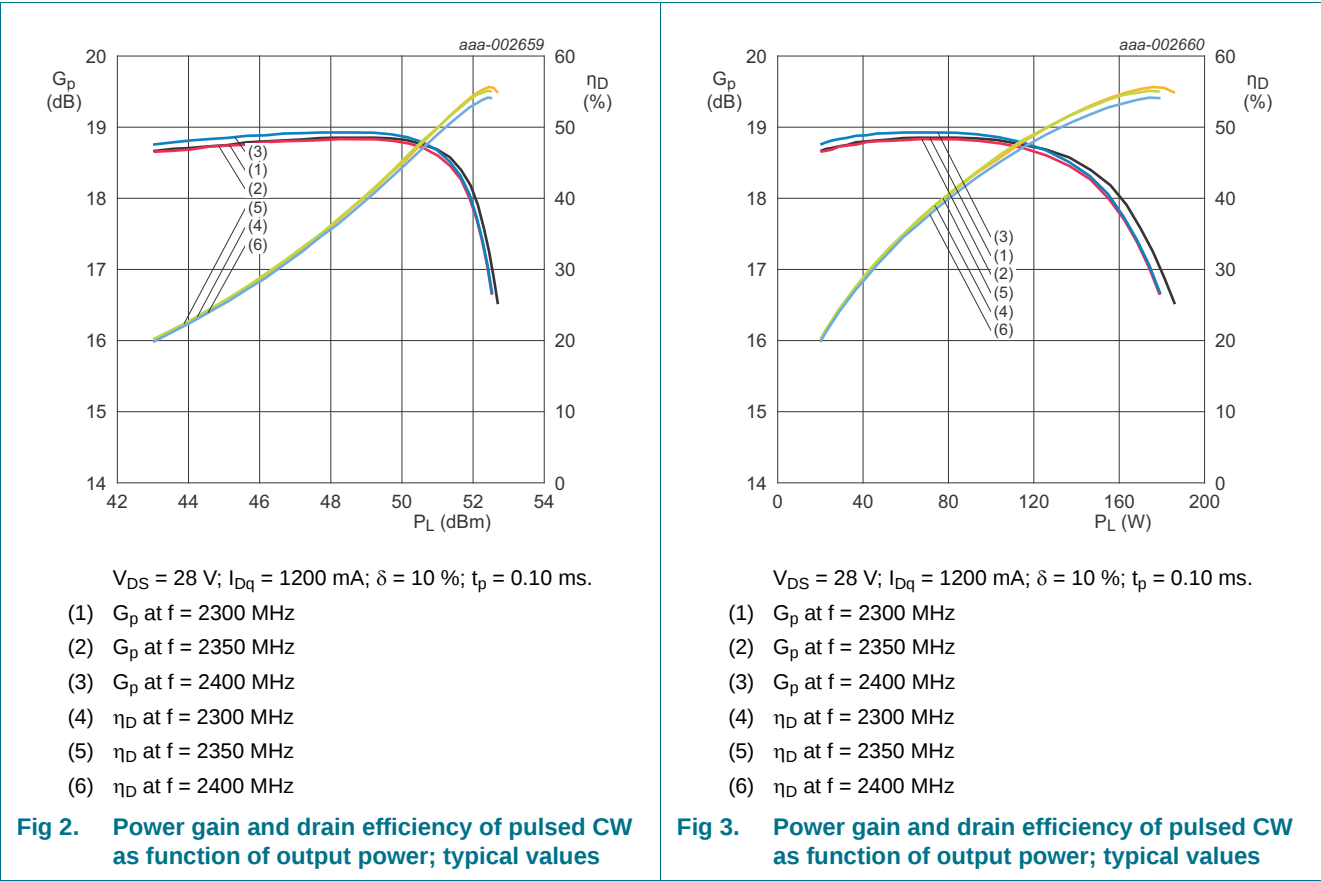
Table 8. Typical impedance
 Measured load-pull data. Typical values per section.
 $I_{Dq} = 600\text{ mA}$; main transistor $V_{DS} = 28\text{ V}$. Z_S and Z_L defined in [Figure 1](#).

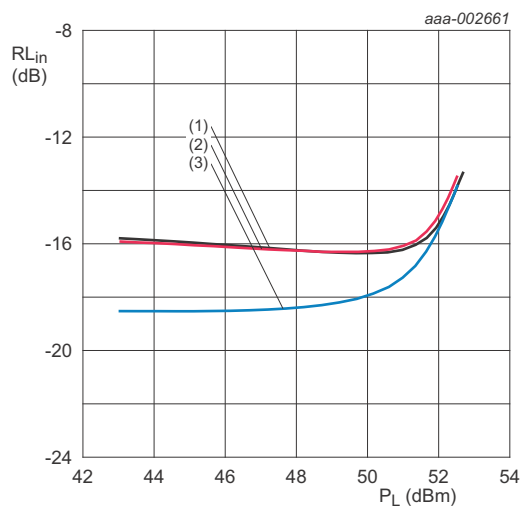
f (MHz)	Z_S (Ω)	Z_L (Ω)
2300	$2.5 - j5.9$	$3.1 - j4.3$
2400	$4.6 - j7.2$	$2.9 - j4.2$



7.3 Graphs

7.3.1 Pulsed CW



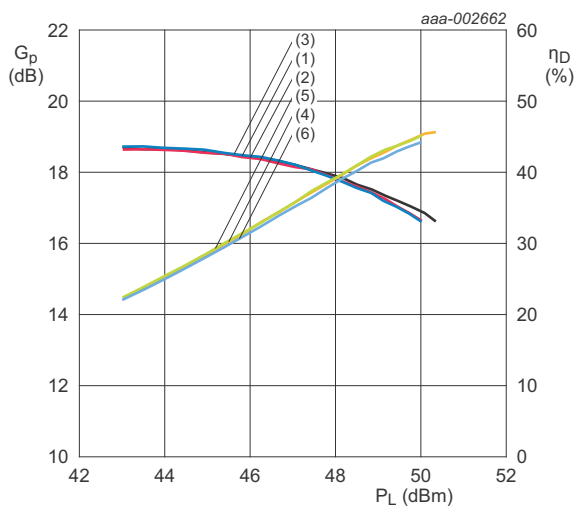


$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$; $\delta = 10\%$; $t_p = 0.10\text{ ms}$.

- (1) $f = 2300\text{ MHz}$
- (2) $f = 2350\text{ MHz}$
- (3) $f = 2400\text{ MHz}$

Fig 4. Input return loss of pulsed CW as a function of output power; typical values

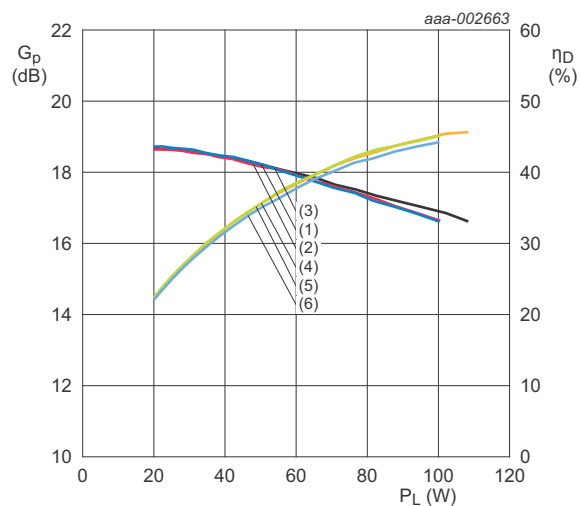
7.3.2 IS-95



$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$.

- (1) G_p at $f = 2300\text{ MHz}$
- (2) G_p at $f = 2350\text{ MHz}$
- (3) G_p at $f = 2400\text{ MHz}$
- (4) η_D at $f = 2300\text{ MHz}$
- (5) η_D at $f = 2350\text{ MHz}$
- (6) η_D at $f = 2400\text{ MHz}$

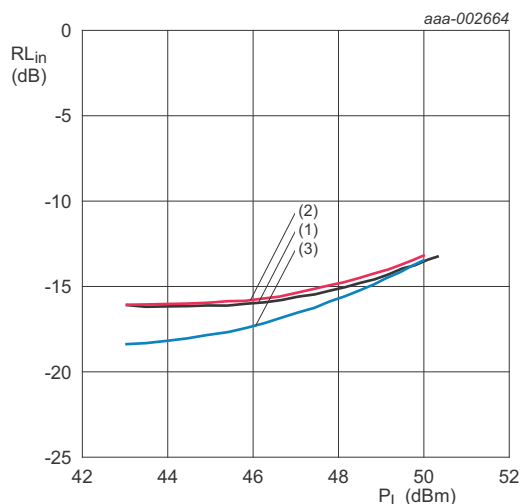
Fig 5. Power gain and drain efficiency of IS-95 as function of output power; typical values



$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$.

- (1) G_p at $f = 2300\text{ MHz}$
- (2) G_p at $f = 2350\text{ MHz}$
- (3) G_p at $f = 2400\text{ MHz}$
- (4) η_D at $f = 2300\text{ MHz}$
- (5) η_D at $f = 2350\text{ MHz}$
- (6) η_D at $f = 2400\text{ MHz}$

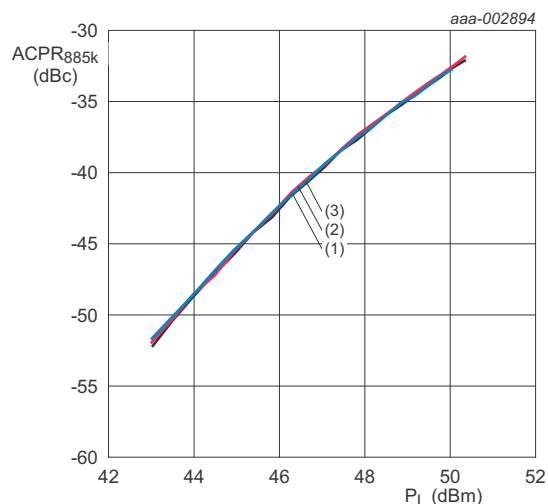
Fig 6. Power gain and drain efficiency of IS-95 as function of output power; typical values



$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$.

- (1) $f = 2300\text{ MHz}$
- (2) $f = 2350\text{ MHz}$
- (3) $f = 2400\text{ MHz}$

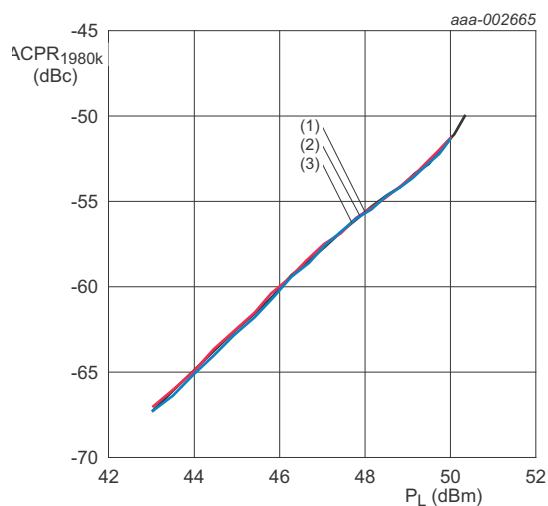
Fig 7. Input return loss of IS-95 as a function of output power; typical values



$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$.

- (1) $f = 2300\text{ MHz}$
- (2) $f = 2350\text{ MHz}$
- (3) $f = 2400\text{ MHz}$

Fig 8. Adjacent channel power ratio (885 kHz) of IS-95 as a function of output power; typical values

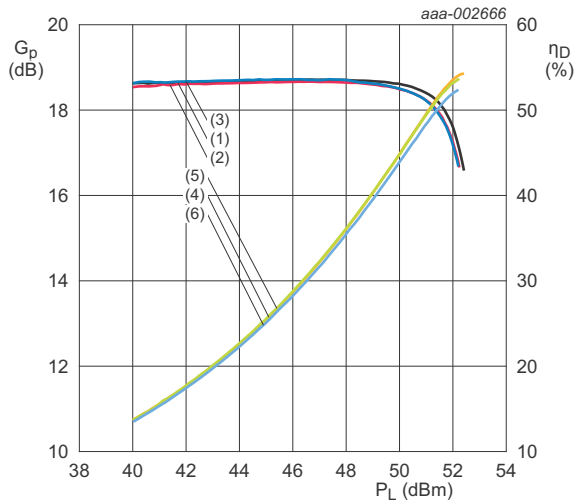


$V_{DS} = 28\text{ V}$; $I_{DQ} = 1200\text{ mA}$.

- (1) $f = 2300\text{ MHz}$
- (2) $f = 2350\text{ MHz}$
- (3) $f = 2400\text{ MHz}$

Fig 9. Adjacent channel power ratio (1980 kHz) of IS-95 as a function of output power; typical values

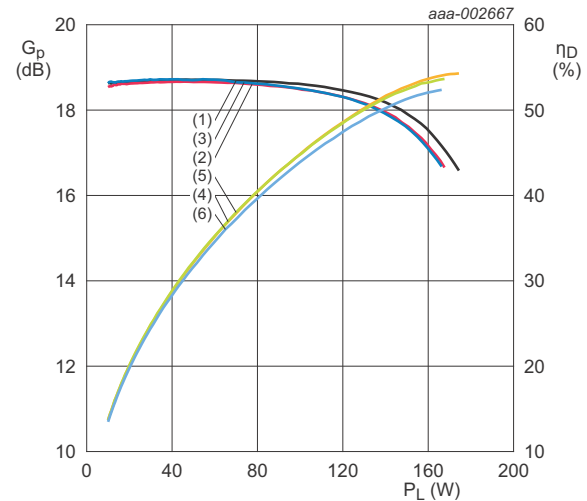
7.3.3 CW



$V_{DS} = 28 \text{ V}$; $I_{DQ} = 1200 \text{ mA}$.

- (1) G_p at $f = 2300 \text{ MHz}$
- (2) G_p at $f = 2350 \text{ MHz}$
- (3) G_p at $f = 2400 \text{ MHz}$
- (4) η_D at $f = 2300 \text{ MHz}$
- (5) η_D at $f = 2350 \text{ MHz}$
- (6) η_D at $f = 2400 \text{ MHz}$

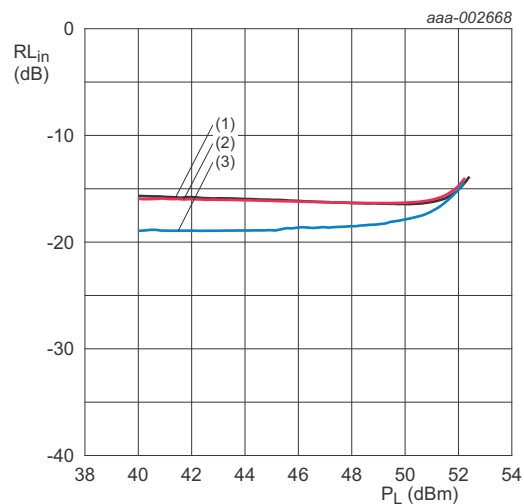
Fig 10. Power gain and drain efficiency of CW as function of output power; typical values



$V_{DS} = 28 \text{ V}$; $I_{DQ} = 1200 \text{ mA}$.

- (1) G_p at $f = 2300 \text{ MHz}$
- (2) G_p at $f = 2350 \text{ MHz}$
- (3) G_p at $f = 2400 \text{ MHz}$
- (4) η_D at $f = 2300 \text{ MHz}$
- (5) η_D at $f = 2350 \text{ MHz}$
- (6) η_D at $f = 2400 \text{ MHz}$

Fig 11. Power gain and drain efficiency of CW as function of output power; typical values



$V_{DS} = 28 \text{ V}$; $I_{DQ} = 1200 \text{ mA}$.

- (1) $f = 2300 \text{ MHz}$
- (2) $f = 2350 \text{ MHz}$
- (3) $f = 2400 \text{ MHz}$

Fig 12. Input return loss of CW as a function of output power; typical values

7.4 Test circuit

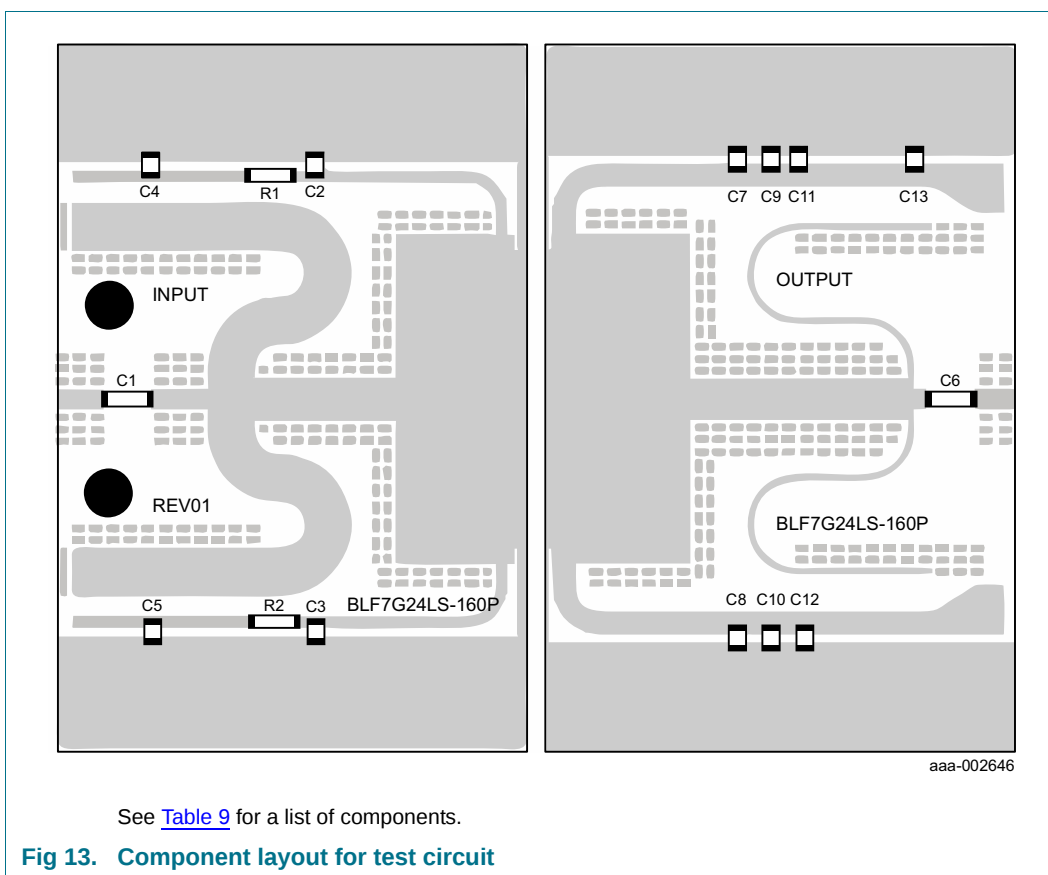


Table 9. List of components

For test circuit, see [Figure 13](#).

Component	Description	Value	Remarks
C1, C6	multilayer ceramic chip capacitor	7.5 pF	[1]
C2, C3, C7, C8	multilayer ceramic chip capacitor	16 pF	[2]
C4, C5, C9, C10	multilayer ceramic chip capacitor	20 nF	[1]
C11, C12	multilayer ceramic chip capacitor	10 μ F	[3]
C13	electrolytic capacitor	220 μ F; 63 V	
R1, R2	chip resistor	2 Ω ; SMD 805	

[1] American technical ceramics type 100B or capacitor of same quality.

[2] American technical ceramics type 100A or capacitor of same quality.

[3] TDK or capacitor of same quality.

8. Package outline

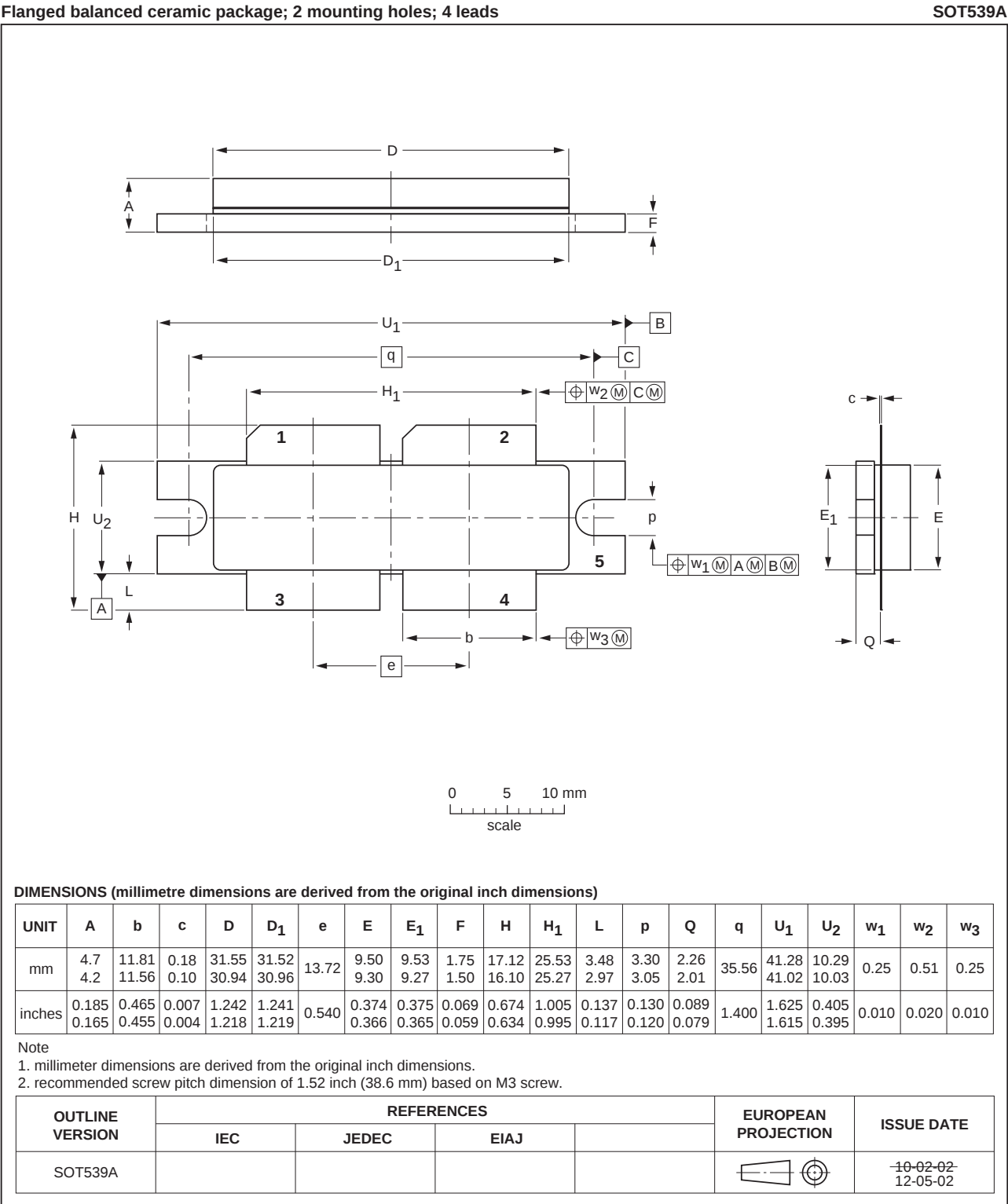
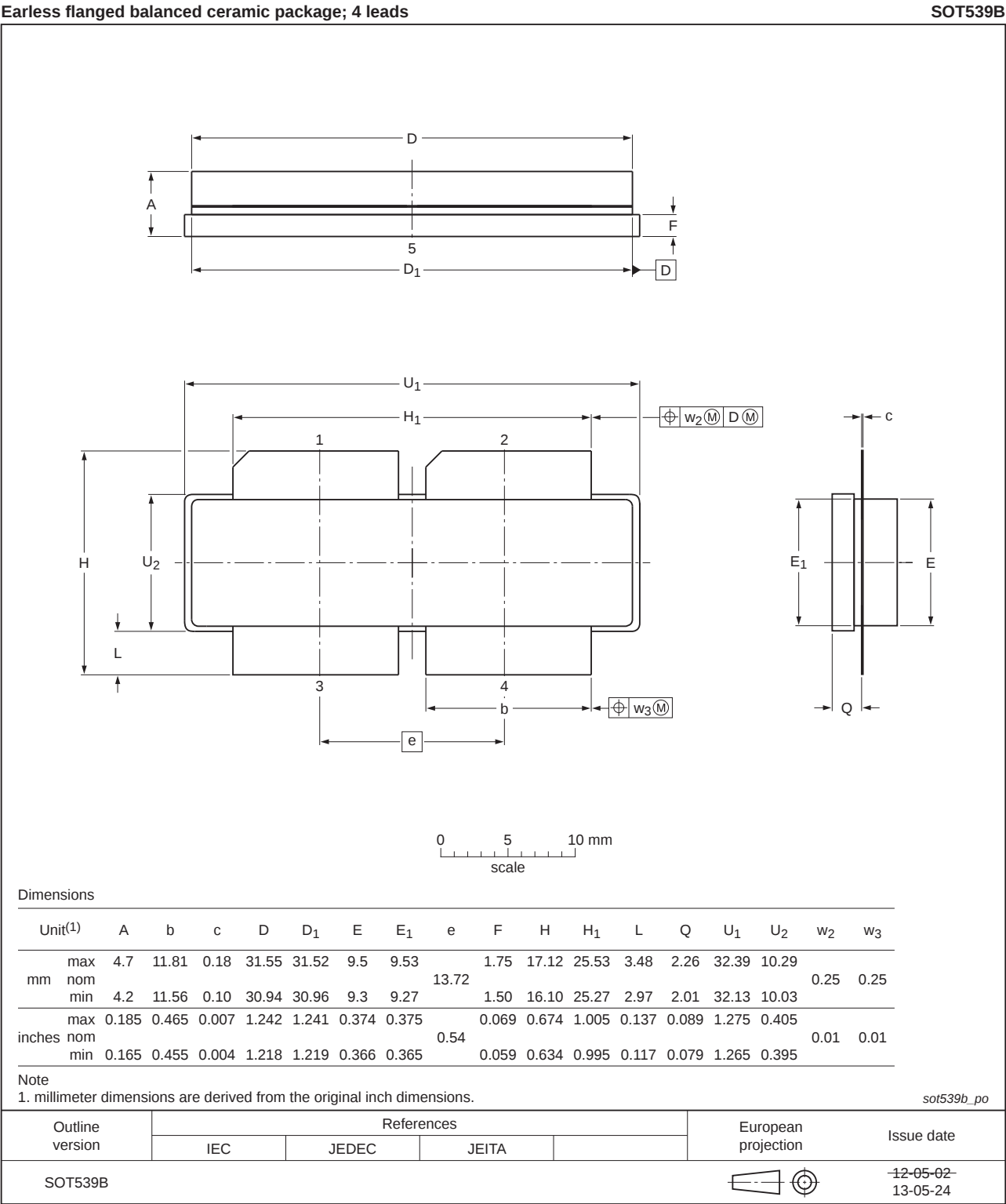


Fig 14. Package outline SOT539A



9. Abbreviations

Table 10. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
IS-95	Interim Standard 95
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio

10. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G24L-160P_7G24LS-160P v.5	20130712	Product data sheet	-	BLF7G24L-160P_7G24LS-160P v.4
Modifications:	The package outline Figure 15 is updated.			
BLF7G24L-160P_7G24LS-160P v.4	20120725	Product data sheet	-	BLF7G24L-160P_7G24LS-160P v.3
Modifications:	- The status of this document has been changed to Product data sheet - Table 6 on page 3: added max. value $R_{DS(on)}$. - Table 7 on page 3: modified max. value of RL_{in}.			
BLF7G24L-160P_7G24LS-160P v.3	20120420	Preliminary data sheet	-	BLF7G24L-160P_7G24LS-160P v.2
BLF7G24L-160P_7G24LS-160P v.2	20120301	Objective data sheet	-	BLF7G24L-160P_7G24LS-160P v.1
BLF7G24L-160P_7G24LS-160P v.1	20120210	Objective data sheet	-	-

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Test information	3
7.1	Ruggedness in class-AB operation	3
7.2	Impedance information	4
7.3	Graphs	4
7.3.1	Pulsed CW	4
7.3.2	IS-95	5
7.3.3	CW	7
7.4	Test circuit	8
8	Package outline	9
9	Abbreviations	11
10	Revision history	11
11	Legal information	12
11.1	Data sheet status	12
11.2	Definitions	12
11.3	Disclaimers	12
11.4	Trademarks	13
12	Contact information	13
13	Contents	14

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